更正: 基于 55 nm DICE 结构的单粒子翻转效应模拟研究

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《物理学报》2024 年第 73 卷第 6 期第 066103 页《基于 55 nm DICE 结构的单粒子翻转效应模拟研究》一文中, 因作者的疏忽导致图文标注错误, 特此更正, 并诚挚地向读者致歉. 图 7(b) 图例内容更正如下:

1) LET 值为 10 MeV·cm^2/mg 时, DA 节点瞬态脉冲宽度为 0.22 ns;

2) LET 值为 15 MeV·cm^2/mg 时, DA 节点瞬态脉冲宽度为 0.30 ns;

3) LET 值为 20 MeV·cm^2/mg 时, DA 节点瞬态脉冲宽度为 0.38 ns.

更正后的图 7 如下所示.

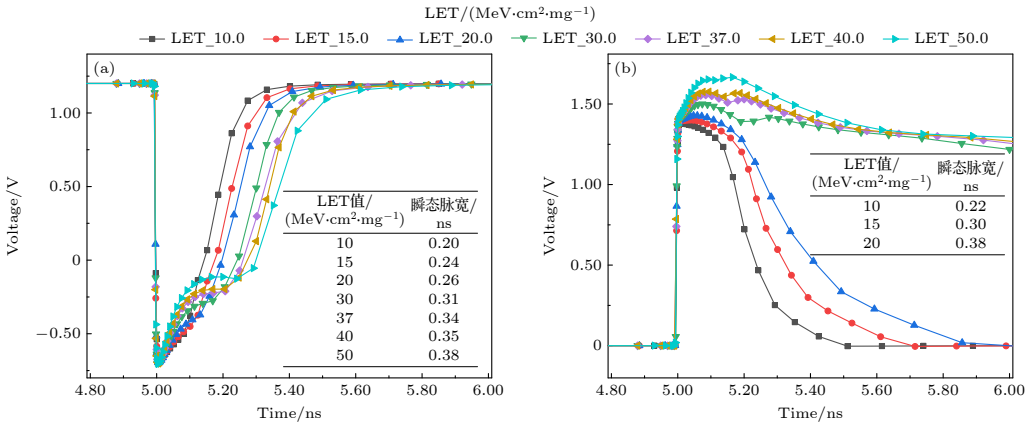

图 7 不同 LET 值入射时 DA 节点电位变化图 (a) 轰击 DN3 晶体管时 DA 节点的电位变化图; (b) 轰击 DP4 晶体管时 DA 节点的电位变化图

Fig. 7. Voltage variation diagram of DA node when particle incidents by different LET value: (a) Voltage variation diagram of DA node when bombarding DN3 transistor; (b) voltage variation diagram of DA node when bombarding DP4 transistor.

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